High Purity and High Mobility Semiconductors 13

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Sponsoring Division:

Electronics and Photonics

Published by
The Electrochemical Society
65 South Main Street, Building D
Pennington, NJ 08534-2839, USA
tel 609 737 1902
fax 609 737 2743
www.electrochem.org

ecs transactions ™

Vol. 64, No. 11

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)
ISSN 2151-2051 (cd-rom)

ISBN 978-1-62332-191-8 (Hard Cover)
ISBN 978-1-60768-548-7 (PDF)

Printed in the United States of America.

ECS Transactions, **Volume 64, Issue 11**
High Purity and High Mobility Semiconductors 13

Table of Contents

Preface *iii*

Chapter 1
Crystal Growth and Point Defects

(Invited) Growth of Czochralski Silicon Crystals with Ultralow Carbon Concentrations for High-Power Insulated-Gate Bipolar Transistor Devices 3
Y. Nagai, S. Nakagawa, M. Higasa, K. Kashima

Absolute Value Determination of Vacancy Concentration in Silicon Crystals Using Low-Temperature Ultrasonic Measurements 13
H. Yamada-Kaneta, K. Okabe, M. Akatsu, S. Baba, K. Mitsumoto, Y. Nemoto, T. Goto, H. Saito, K. Kashima, Y. Saito

Highly Sensitive and Accurate Infrared Absorption Measurement of Carbon Concentration in Si Crystal 19
N. Inoue, K. Watanabe, H. Seki, H. Uno, H. Oyama, Y. Kawamura

Chapter 2
Oxygen in Silicon

(Invited) Oxygen Precipitation and Defect Generation in Cz Silicon during Second and Millisecond Annealing 29
G. H. Kissinger, D. Kot, M. A. Schubert, A. Sattler

(Invited) Modeling of Oxygen Precipitation in Silicon 45
S. T. Dunham, B. C. Trzynadlowski

Precipitation Behaviors of Rapid Thermal Annealing Treated Silicon Wafers under Various Thermal Cycles 55
D. Lee, T. Kim, S. Park, T. Kim, Y. Lee, E. Park, H. Yeo, R. Falster

Morphology of Oxygen Precipitates in RTA Pre-Treated Czochralski Silicon Wafers Investigated by FTIR Spectroscopy and STEM 71
D. Kot, G. Kissinger, M. A. Schubert, A. Sattler

Chapter 3
Epitaxy for Strain Engineering

(Keynote) Epitaxy-Based Strain-Engineering Methods for Advanced Devices 85
D. Grützmacher, S. Wirths, T. Rieger, D. Buca, T. Stoica, M. I. Lepsa, Q. T. Zhao, S. Mantl

Chapter 4
High Mobility Materials and Advanced Devices

(Keynote) Material Challenges and Opportunities in Ge/III-V Channel MOSFETs 99
S. Takagi, S. H. Kim, M. Yokoyama, K. Nishi, R. Zhang, M. Takenaka

(Invited) First-Principles Studies of the Defect Formation in III-V FETs Grown by Fin Replacement Method 111
H. Minari, S. Yoshida, K. Sawada, M. Nakazawa, M. Caymax, C. Merckling, N. Waldron, W. Guo, S. Jiang, N. Collaert, E. Simoen, D. Lin, G. Pourtois

Chapter 5
Ge-based Devices

(Invited) The Impact of a (Si)Ge Heterojunction on the Analog Performance of Vertical Tunnel FETs 127
P. G. D. Agopian, J. A. Martino, A. Vandooren, R. Rooyackers, E. Simoen, A. Thean, C. Claeys

(Invited) Ge-on-Insulator MOSFETs for High-Performance and 3D-LSI Applications 135
T. Tezuka, K. Ikeda, Y. Kamata, Y. Kamimuta, K. Usuda, Y. Moriyama, M. Ono, M. Koike, M. Oda, T. Irisawa, E. Mieda, T. Maeda, W. Jevasuwan, Y. Kurashima, H. Takagi, K. Furuse, E. Kurosawa

(Invited) Solid Phase Epitaxy of GeSn Alloys on Silicon and Integration in MOSFET Devices 149
R. R. Lieten, T. Maeda, J. W. Seo, W. Jevasuwan, H. Hattori, N. Uchida, S. Miura, M. Tanaka, C. Fleischmann, A. Vantomme, B. C. Johnson, J. P. Locquet

Chapter 6
Doping and Junctions

(Invited) Alternative High n-Type Doping Techniques in Germanium 163
G. Capellini, W. M. Klesse, G. Mattoni, M. Y. Simmons, G. Scappucci

Deep-Level Defects in High-Dose Proton Implanted and High-Temperature Annealed Silicon 173
M. Jelinek, J. Laven, M. Rommel, W. Schustereder, H. J. Schulze, L. Frey, R. Job

Formation of Shallow n-p Junctions in Cz-Si by Low-Energy Implantation of Carbon Ions 187
B. Romanyuk, V. Melnik, V. Popov, V. Litovchenko, V. Babich, V. Ilchenko, V. Kladko, J. Vanhellemont

A New Method to Increase the Doping Efficiency of Proton Implantation in a High-Dose Regime 199
M. Jelinek, J. Laven, R. Job, W. Schustereder, H. J. Schulze, M. Rommel, L. Frey

Chapter 7
Metals and Gettering

Modeling of Carbon Clustering and Associated Metal Gettering 211
Y. Jin, S. T. Dunham

Deep Levels in W-Doped Czochralski Silicon 219
E. Simoen, K. Saga, J. Lauwaert, H. Vrielinck

Ab Initio Analysis on Stability of Metal Atoms in β-Si_3N_4/Si Structure 229
D. Shibata, S. Kobayashi, K. Sueoka, J. Komachi, K. Saga

Chapter 8
Characterization

(Invited) Positron Annihilation Spectroscopy on Open-Volume Defects in Group IV Semiconductors — 241
J. Slotte, F. Tuomisto, J. Kujala, A. M. Holm, N. Segercrantz, S. Kilpeläinen, K. Kuitunen, E. Simoen, F. Gencarelli, R. Loo, Y. Shimura

(Invited) Synchrotron Radiation Based X-ray Microdiffraction of Advanced Semiconductor Materials — 255
A. Sakai

Chapter 9
Point and Extended Defects

(Invited) Single Dislocations as Nanostructure Devices: Physics and Applications — 267
M. Reiche, M. Kittler, H. Uebensee, E. Pippel, W. Erfurth

Temperature Dependent Young's Modulus of Si and Ge — 283
J. Vanhellemont, A. K. Swarnakar, O. Van der Biest

(Invited) Nature of Point Defects at High-Mobility Semiconductor/Interfaces Probed by Electron Spin Resonance: Thermal GaAs/GaAs-Oxide Structures — 293
A. Stesmans, S. Nguyen, V. V. Afanas'ev

Author Index — 301